

isc N-Channel MOSFET Transistor

IRF640N

DESCRIPTION

- Drain Current $-I_D = 18A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 200V (Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.15 \Omega (Max)$
- Fast Switching Speed
- Low Drive Requirement

APPLICATIONS

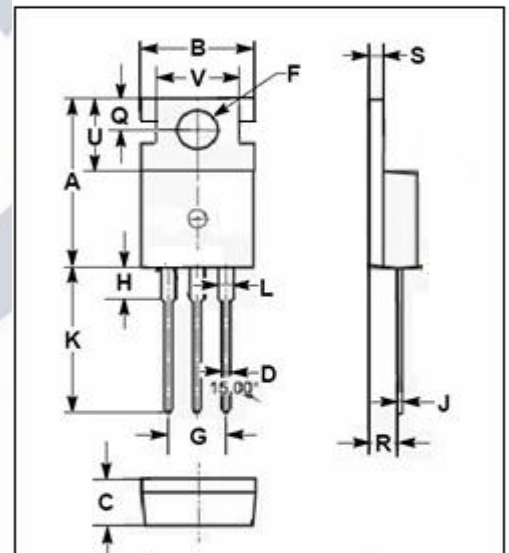
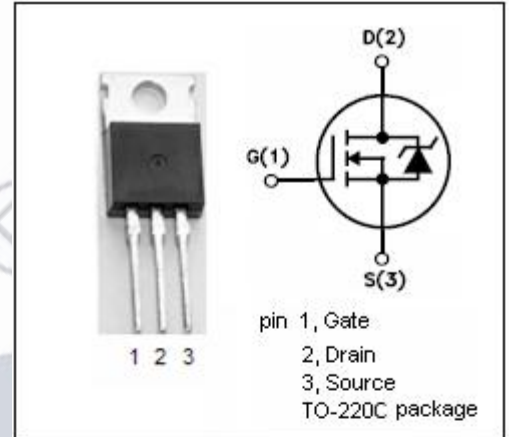
- Designed for low voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC = 25^\circ C$	18	A
P_{tot}	Total Dissipation@ $TC = 25^\circ C$	150	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc N-Channel Mosfet Transistor**IRF640N****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	200		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 11A		0.15	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V; V _{GS} = 0		25	uA
V _{SD}	Diode Forward Voltage	I _F = 11A; V _{GS} =0		1.3	V